	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	151646	438/$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L3	59	1 and ((phase-change near memory) or phase-change-memory or (phase near change near memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L4	44	3 and (trench or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L5	40	4 and resistivity	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L6	42	dennison-charles.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L7	13	6 and ((phase-change near memory) or phase-change-memory or (phase near change near memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L8	147	((phase-change near memory) or phase-change-memory or (phase near change near memory)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L9	42	8 and (trench or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L10	416	((phase-change near memory) or phase-change-memory or (phase near change near memory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L11	120	10 and (trench or recess)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L12	13	11 and (angl$3 near dop$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	